



40V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D T _A = +25°C
40V	$24m\Omega @V_{GS} = 10V$	9.0A
400	$32mΩ @V_{GS} = 4.5V$	7.8A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Backlighting
- Power Management Functions
- DC-DC Converters

Features

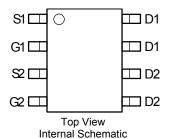
- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

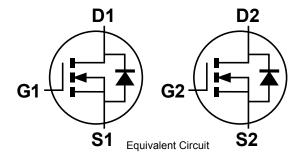
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram below
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.074 grams (approximate)









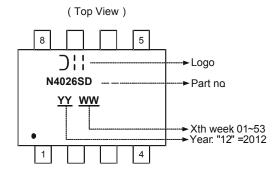
Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Packaging
DMN4026SSD-13	Standard	SO-8	2,500/Tape & Reel
DMN4026SSDQ-13	Automotive	SO-8	2.500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic Drain-Source Voltage			Symbol	Value	Units V
			V _{DSS}	40	
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Dusin Courset (Note 7) / - 40/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	7.0 5.6	А
Continuous Drain Current (Note 7) V _{GS} = 10V	T<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	9.0 7.2	А
Maximum Continuous Body Diode Forward Current (Note 7)			Is	2.5	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	70	Α

Thermal Characteristics

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)	T _A = +25°C	D	1.3	W
Total Fower Dissipation (Note 6)	T _A = +70°C	P_{D}	0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	98	°C/W
Thermal Resistance, Junction to Ambient (Note 0)	t<10s	$R_{\theta JA}$	59	
Total Power Dissipation (Note 7)	T _A = +25°C	D-	1.8	W
Total Fower Dissipation (Note 1)	T _A = +70°C	P_{D}	1.1	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	D	71	°C/W
Thermal Resistance, Junction to Ambient (Note 1)	t<10s	$R_{\theta JA}$	43	
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	11.8		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

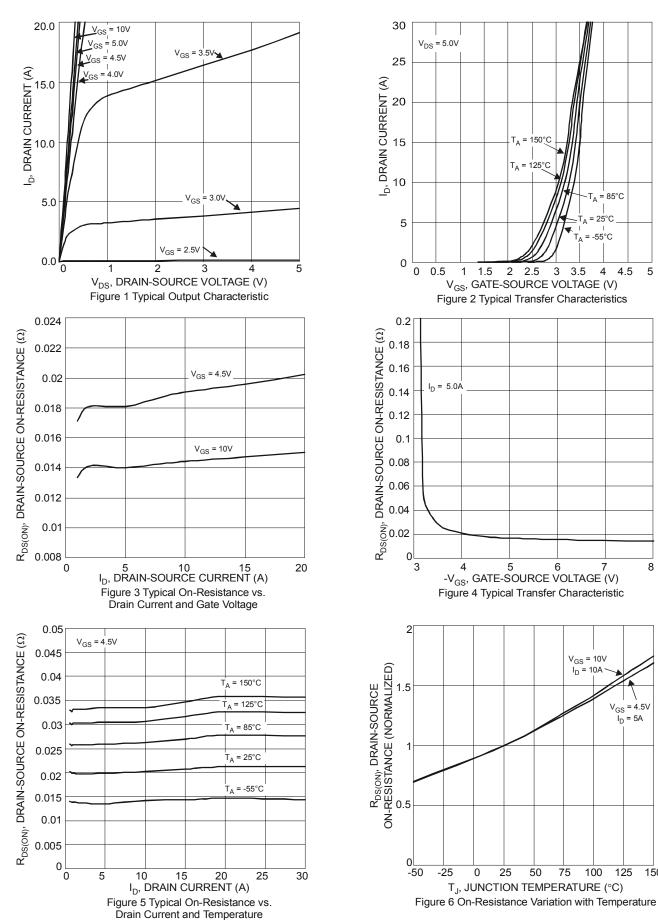
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 40V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	15	24	mΩ	V _{GS} = 10V, I _D = 6A	
Static Drain-Source On-Resistance	R _{DS(ON)}		20	32		V _{GS} = 4.5V, I _D = 5A	
Diode Forward Voltage	V_{SD}		0.7	1.0	V	V _{GS} = 0V, I _S = 1.0A	
DYNAMIC CHARACTERISTICS (Note 9)	· · · · · · · · · · · · · · · · · · ·						
Input Capacitance	C _{iss}		1060	_		.,	
Output Capacitance	Coss	_	84	_	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		58	_			
Gate Resistance	R_G	_	1.6	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	8.8	20			
Total Gate Charge (V _{GS} = 10V)	Qg	_	19.1	43			
Gate-Source Charge	Q_{gs}		3.0	7.5	nC	$V_{DS} = 20V, I_{D} = 8A$	
Gate-Drain Charge	Q_{gd}		2.5	6			
Turn-On Delay Time	t _{D(on)}		5.3	_		$V_{DD} = 25V, R_L = 2.5\Omega$	
Turn-On Rise Time	t _r	_	7.1	_	- C		
Turn-Off Delay Time	t _{D(off)}		15.1	_	nS	V_{GS} = 10V, R_G = 3 Ω	
Turn-Off Fall Time	t _f		4.8	_			
Body Diode Reverse Recovery Time	t _{rr}		10.5	_	nS	I _F = 8A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Qrr		4.15	_	nC	I _F = 8A, di/dt = 100A/μs	

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- ${\bf 8.\ Short\ duration\ pulse\ test\ used\ to\ minimize\ self-heating\ effect.}$
- 9. Guaranteed by design. Not subject to product testing.

= 85°C

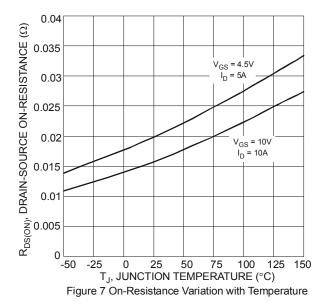




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V_{GS} = 4.5V I_D = 5A





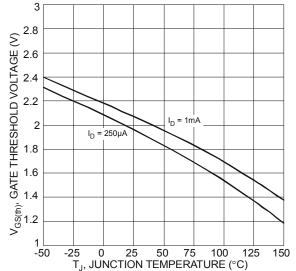
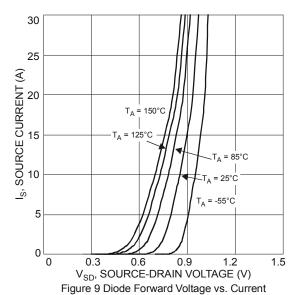
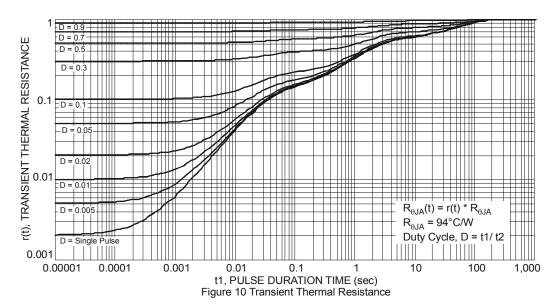


Figure 8 Gate Threshold Variation vs. Ambient Temperature

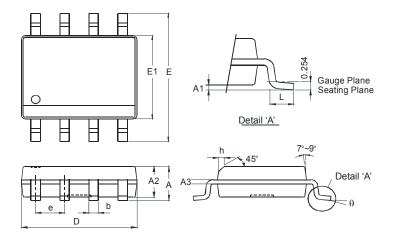






Package Outline Dimensions

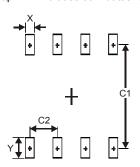
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8					
Dim	Min	Max			
Α	1	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	1	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)		
X	0.60		
Y	1.55		
C1	5.4		
C2	1.27		



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